

isc Silicon NPN RF Transistor

2SC2408

**DESCRIPTION**

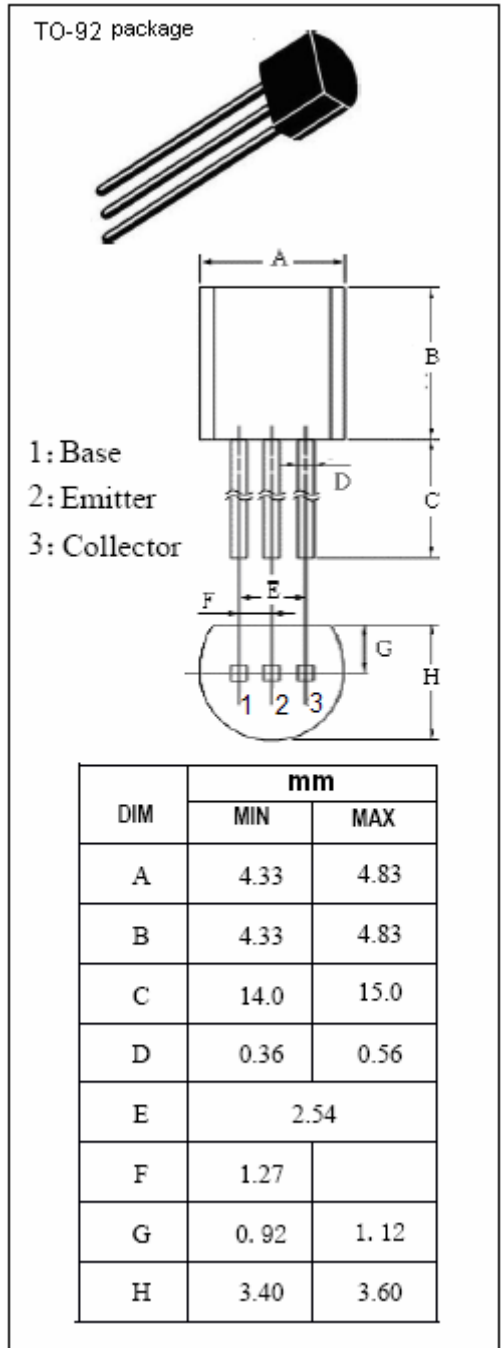
- Low Noise  
 $NF = 2.4 \text{ dB TYP. ;@ } f = 200 \text{ MHz}$
- High Gain  
 $|S_{21e}|^2 = 21 \text{ dB TYP. ;@ } f = 200 \text{ MHz}$

**APPLICATIONS**

- Designed for use in high frequency wide band amplifier.

**ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	35	V
V <sub>CEO</sub>	Collector-Emitter Voltage	18	V
V <sub>EBO</sub>	Emitter-Base Voltage	3	V
I <sub>C</sub>	Collector Current-Continuous	150	mA
P <sub>C</sub>	Collector Power Dissipation @T <sub>C</sub> =25°C	0.6	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=20\text{V}; I_E=0$			0.5	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=2\text{V}; I_C=0$			0.5	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C=50\text{mA}; V_{CE}=10\text{V}$	30		200	
$f_T$	Current-Gain—Bandwidth Product	$I_C=50\text{mA}; V_{CE}=10\text{V}$		3.5		GHz
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f=1.0\text{MHz}$		1.25	2.0	pF
$ S_{21e} ^2$	Insertion Power Gain	$I_C=50\text{mA}; V_{CE}=10\text{V}; f=200\text{MHz}; R_G=50\Omega$	18	21		dB
NF	Noise Figure	$I_C=30\text{mA}; V_{CE}=10\text{V}; f=200\text{MHz}; R_G=50\Omega$		2.4	4.0	dB